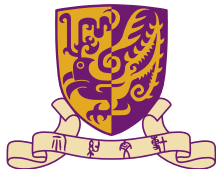


# A Unified Framework for Simultaneous Layout Decomposition and Mask Optimization

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cādence

# Outline

Introduction

Algorithms

Experimental Results

Conclusion

# Outline

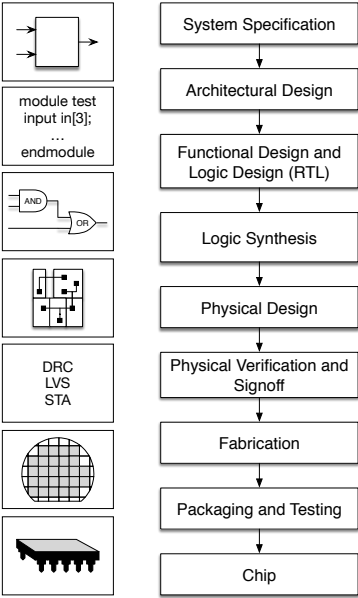
Introduction

Algorithms

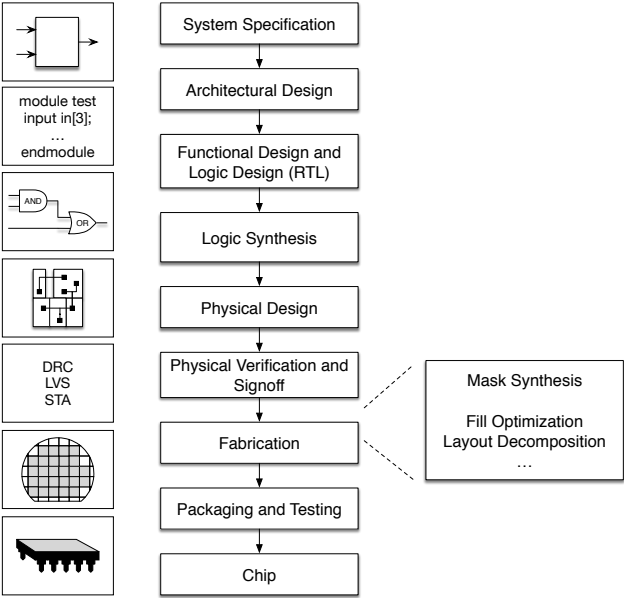
Experimental Results

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# VLSI Chip Design Flow

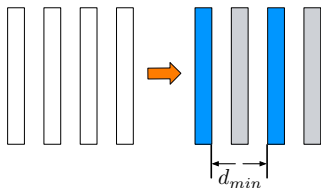


# VLSI Chip Design Flow

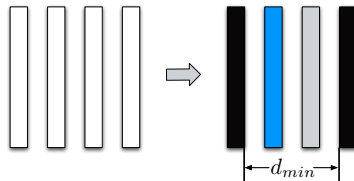


# Layout Decomposition (LD)

- **Conflict:** two features with the same color, while distance  $< d_{min}$



(a) LELE



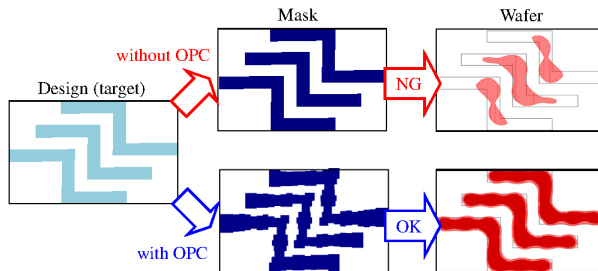
(b) LELELE

## Problem Formulation

**Input:** layout and  $d_{min}$

**Output:** decomposed layout, minimizing conflict #

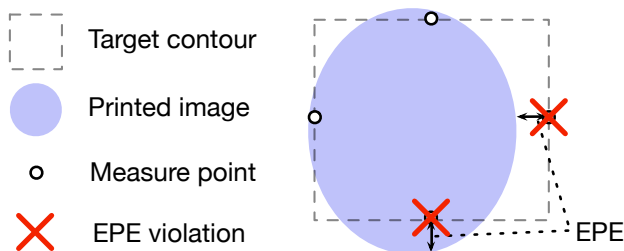
# Mask Optimization (MO)



- ▶ The quality of printed image may be poor due to the diffraction effect of the light.
- ▶ **Optical Proximity Correction(OPC):** Refine the mask to compensate the diffraction effect.
- ▶ Method for OPC:
  - rule-based [Park+,ISQED'2010];
  - model-based [Kuang+,DATE'2015][Su+,TCAD'2016];
  - inverse lithography technique [Gao+,DAC'2014].

## Mask Optimization (cont.)

- ▶ **Edge Placement Error (EPE):** Geometric displacement between the image contour and the edge of target image on the layout.
- ▶ **EPE Violation:** The perpendicular displacement is greater than an EPE threshold value.



### Problem Formulation

**Input:** target layout

**Output:** refined mask, minimizing EPE violation #.

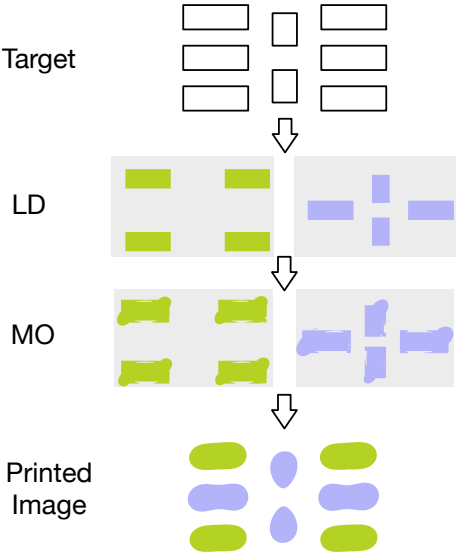




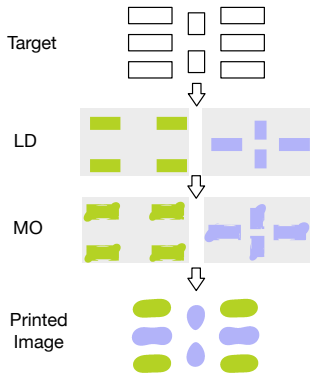
# Two-Stage Flow for Layout Optimization

Two stages:

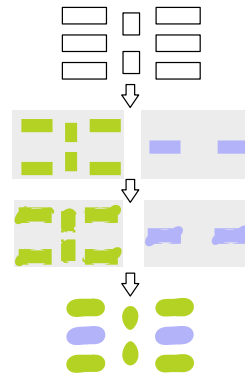
- ▶ Layout Decomposition (LD)
- ▶ Mask Optimization (MO)



# Issues



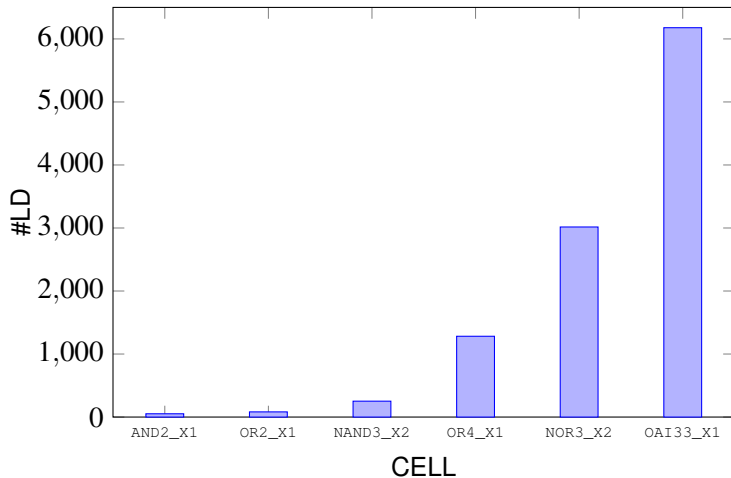
Solution 1: #EPE Violation = 1



Solution 2: #EPE Violation = 3

# Options?

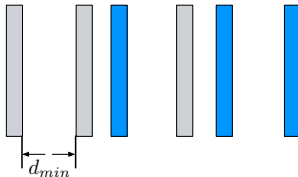
- ▶ **Exhaustive MO** for all LD solutions.
  - Running time overhead due to thousands of LD solutions.



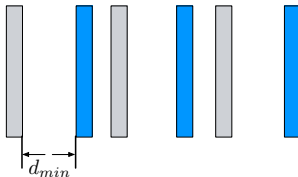
# Options? (cont.)

► **Heuristic selection** among LD solutions.

- Local region density [Yu+,ICCAD'13]: balance the pattern density on each mask.



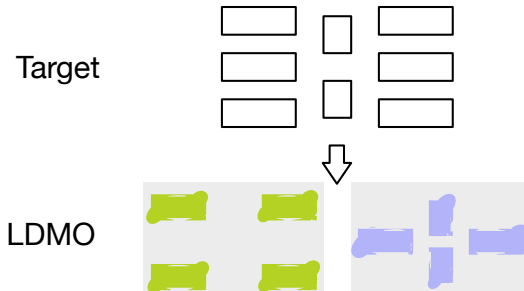
- Spacing vector [Chen+,ISQED'13]: maximize minimum distance between patterns.



- Limited effectiveness.

# Motivation

How about combining LD and MO together?



- ▶ It is an open problem.
- ▶ It is expected to be more effective and more efficient.

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# Preliminaries

► Lithography model:

- The aerial image is formed by a series of convolution operation between mask  $\mathbf{M}$  and lithography kernel  $\mathbf{h}$ .

$$\mathbf{I} = f_{optical}(\mathbf{M}) = \sum_{k=1}^K w_k \cdot |\mathbf{M} \otimes \mathbf{h}_k|^2$$

► Photo-resist model

- Set a threshold  $I_{th}$  to binarize aerial image.

$$\mathbf{Z}(x, y) = f_{resist}(\mathbf{I}) = \begin{cases} 1, & \text{if } \mathbf{I}(x, y) \geq I_{th}, \\ 0, & \text{otherwise.} \end{cases}$$

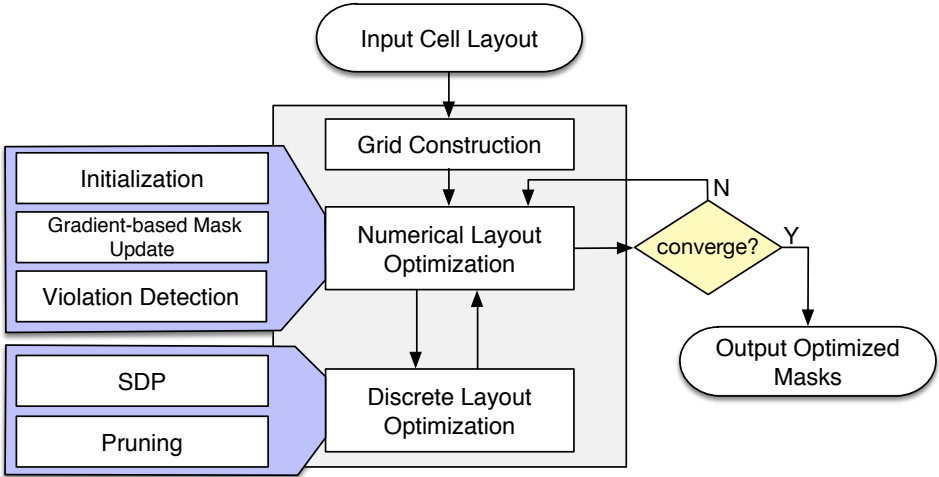
# Problem Formulation

**LDMO:** Given a target image  $\mathbf{Z}_t$ , find two masks  $\mathbf{M}_1$  and  $\mathbf{M}_2$  which can form printed image with high fidelity.

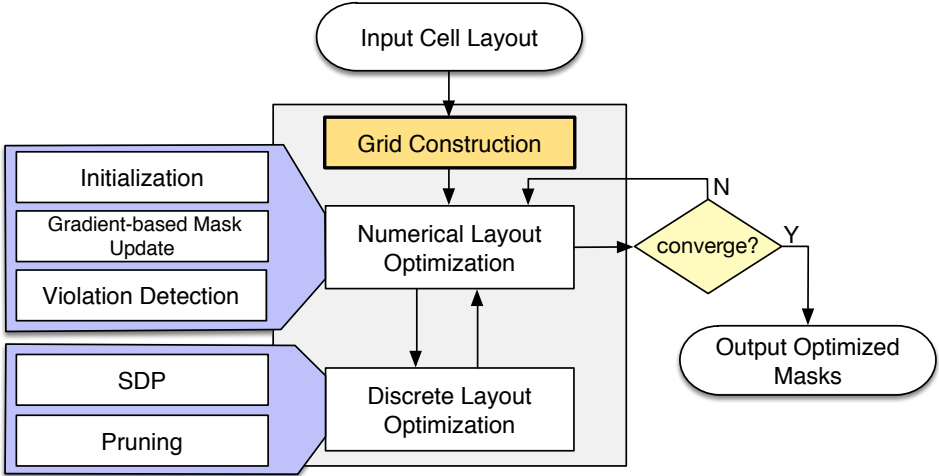
$$\begin{aligned} \min_{\mathbf{M}_1, \mathbf{M}_2} \quad & F = \|\mathbf{Z}_t - \mathbf{Z}\|_2^2 \\ \text{s.t.} \quad & \mathbf{M}_1(x, y) \in \{0, 1\}, \quad \forall x, y, \\ & \mathbf{M}_2(x, y) \in \{0, 1\}, \quad \forall x, y, \\ & \mathbf{I}_1 = \sum_{k=1}^K w_k \cdot |\mathbf{M}_1 \otimes \mathbf{h}_k|^2, \\ & \mathbf{I}_2 = \sum_{k=1}^K w_k \cdot |\mathbf{M}_2 \otimes \mathbf{h}_k|^2, \\ & \mathbf{Z} = f_{resist}(\mathbf{I}_1) \vee f_{resist}(\mathbf{I}_2). \end{aligned}$$



# Overall Flow

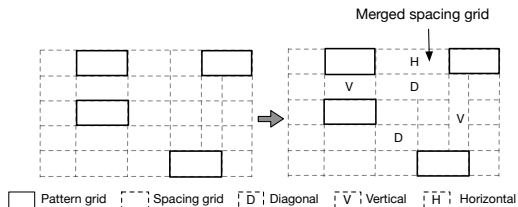
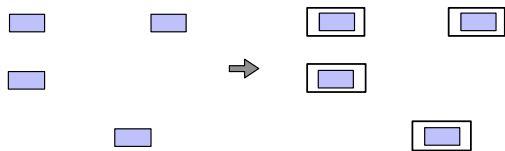


# Overall Flow

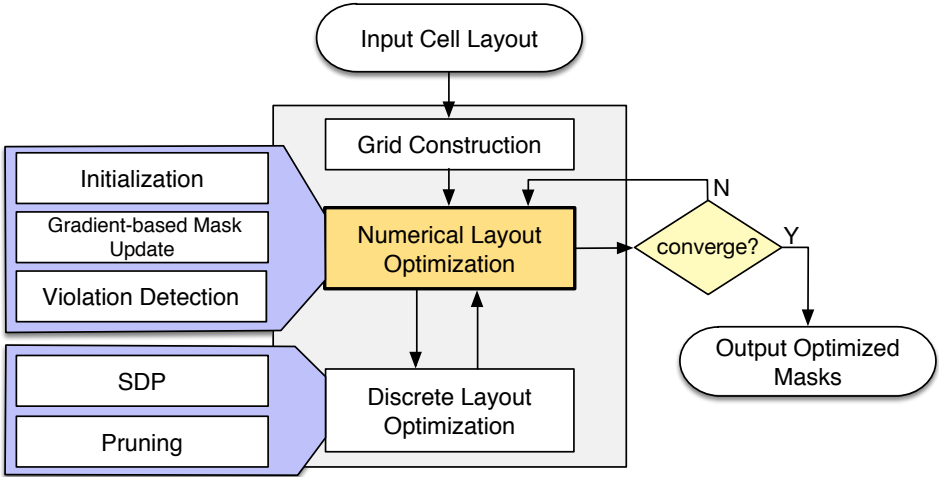


# Grid Construction

- ▶ Extract target pattern.
- ▶ Add bounding box.
- ▶ Construct grid.
- ▶ Merge grid.



# Overall Flow



# Formulation Relaxation

- ▶ Relaxation on binary constraints with *sigmoid* function.

$$\mathbf{M}_1(x, y) \in \{0, 1\} \rightarrow \mathbf{M}_1(x, y) = \text{sig}(\mathbf{P}_1(x, y)) = \frac{1}{1 + \exp[-\theta_M \mathbf{P}_1(x, y)]}$$

$$\mathbf{Z}_1(x, y) = f_{resist}(\mathbf{I}_1) \rightarrow \mathbf{Z}_1(x, y) = \text{sig}(\mathbf{I}_1(x, y)) = \frac{1}{1 + \exp[-\theta_Z(\mathbf{I}_1(x, y) - I_{th})]}$$

- ▶ Relaxation on  $\mathbf{Z}$ .

$$\mathbf{Z} = f_{resist}(\mathbf{I}_1) \vee f_{resist}(\mathbf{I}_2) \rightarrow \mathbf{Z}(x, y) = \min\{\mathbf{Z}_1(x, y) + \mathbf{Z}_2(x, y), 1\}$$

# Gradient-Based Optimization

---

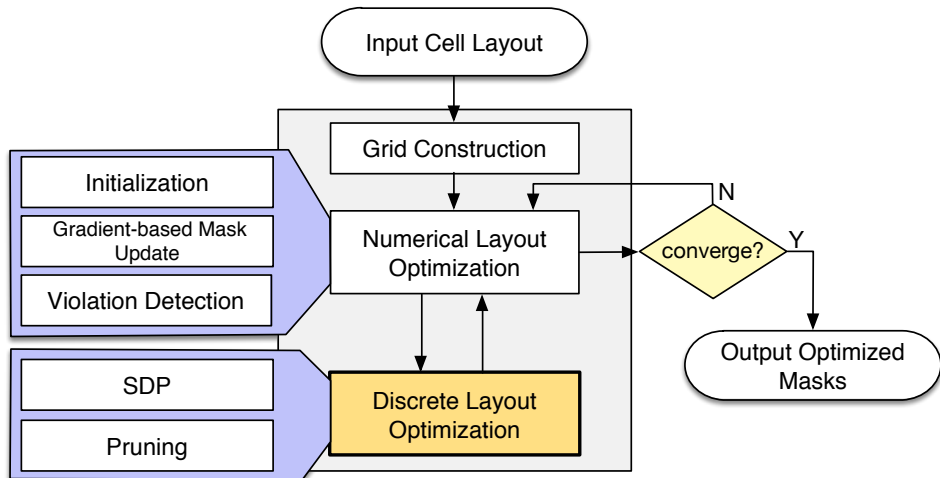
## Algorithm 1 Gradient-Based Mask Update

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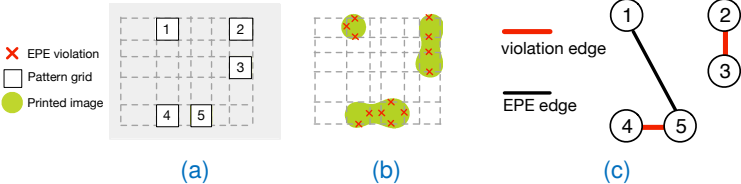
```
1: function MASKUPDATE( $\mathbf{P}_1, \mathbf{P}_2$ )
2:   Initialize stepsize  $t$ ;
3:   Compute the relaxed masks  $\mathbf{M}_1, \mathbf{M}_2$ ;
4:   Compute  $\mathbf{Z}$  according to current  $\mathbf{P}_1$  and  $\mathbf{P}_2$ ;
5:   Compute the gradient  $\nabla_{\mathbf{P}_1} F, \nabla_{\mathbf{P}_2} F$ 
6:    $\mathbf{P}_1 \leftarrow \mathbf{P}_1 - t \times \nabla_{\mathbf{P}_1} F$ ;
7:    $\mathbf{P}_2 \leftarrow \mathbf{P}_2 - t \times \nabla_{\mathbf{P}_2} F$ ;
8:   return  $\mathbf{P}_1, \mathbf{P}_2, \nabla_{\mathbf{P}_1} F, \nabla_{\mathbf{P}_2} F$ ;
9: end function
```

---

# Overall Flow



# Violation Graph



$$w_{ij} = \begin{cases} 1, & \text{if } v_i \text{ and } v_j \text{ have conflict,} \\ \beta, & \text{if } v_i \text{ and } v_j \text{ have large \#EPEV,} \\ 0, & \text{otherwise.} \end{cases}$$

$$\mathbf{W} = \begin{bmatrix} 0 & 0 & 0 & 0 & \beta \\ 0 & 0 & 1 & 0 & 0 \\ 0 & 1 & 0 & 0 & 0 \\ 0 & 0 & 0 & 0 & 1 \\ \beta & 0 & 0 & 1 & 0 \end{bmatrix}$$



# Semidefinite Programming

- ▶ Use  $\mathbf{x} = [x_1, x_2, \dots, x_n]^T$  to denote the grid assignment solution.
- ▶ Max-Cut:

$$\begin{aligned} \max_{x_i} \quad & \sum_{(i,j) \in E} w_{ij}(1 - x_i x_j) \\ \text{s.t.} \quad & x_i \in \{-1, 1\}, \quad \forall v_i \in V \end{aligned}$$

## Relax to Semidefinite Programming:

$$\begin{aligned} \min_{\mathbf{X}} \quad & \mathbf{W} \bullet \mathbf{X} \\ \text{s.t.} \quad & \text{diag}(\mathbf{X}) = \mathbf{e}, \\ & \mathbf{X} \succeq \mathbf{0} \end{aligned}$$

# Semidefinite Programming (cont.)

► Randomized rounding [Goemans+,JACM'1995]

- Obtain  $\mathbf{X}^*$  by solving SDP.
- Cholesky decomposition with  $\mathbf{X}^*$ .

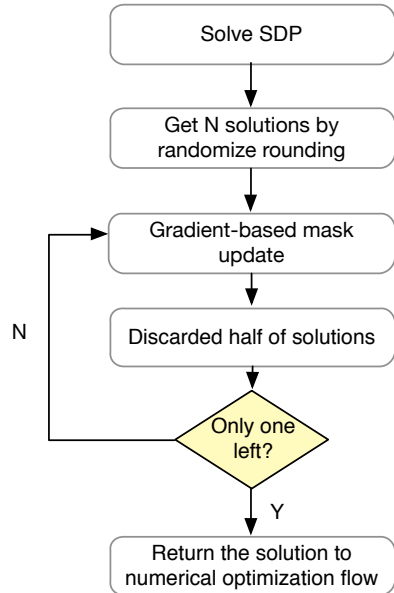
$$\mathbf{X}^* = \mathbf{U}^T \mathbf{U}$$

- Get  $x_i$  as follows.  $\mathbf{u}_i$  is the  $i$ -th column of  $\mathbf{U}$  and  $\mathbf{r}$  is random unit vector.

$$x_i = \text{sgn}(\mathbf{u}_i^T \mathbf{r}) = \begin{cases} 1, & \text{if } \mathbf{u}_i^T \mathbf{r} \geq 0, \\ -1, & \text{otherwise.} \end{cases}$$

# Pruning

- ▶ Obtain multiple solutions by randomized rounding.
- ▶ Efficient pruning.



# Outline

Introduction

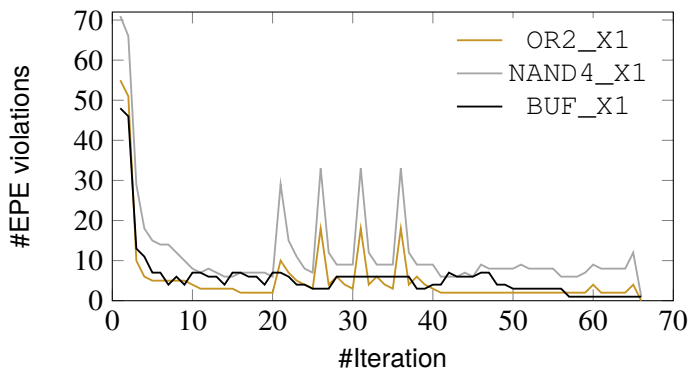
Algorithms

Experimental Results

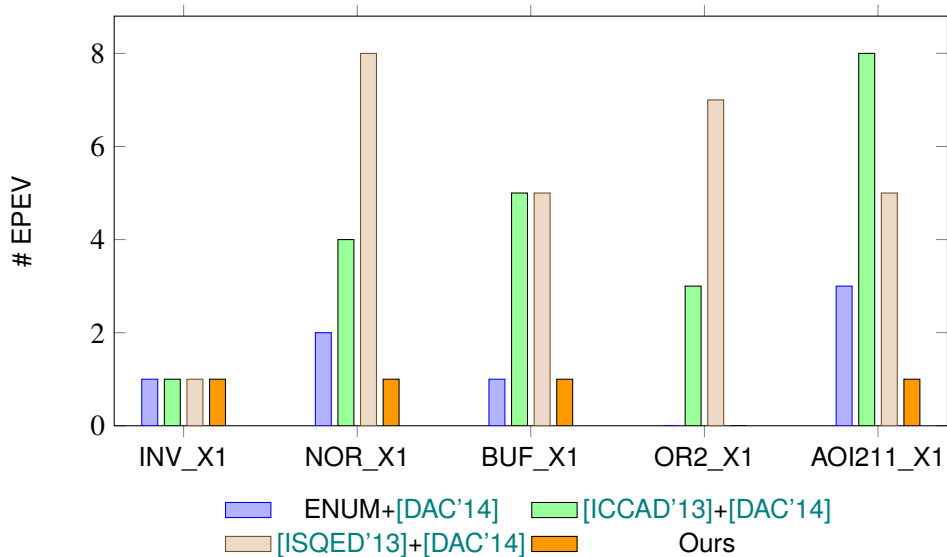
Conclusion



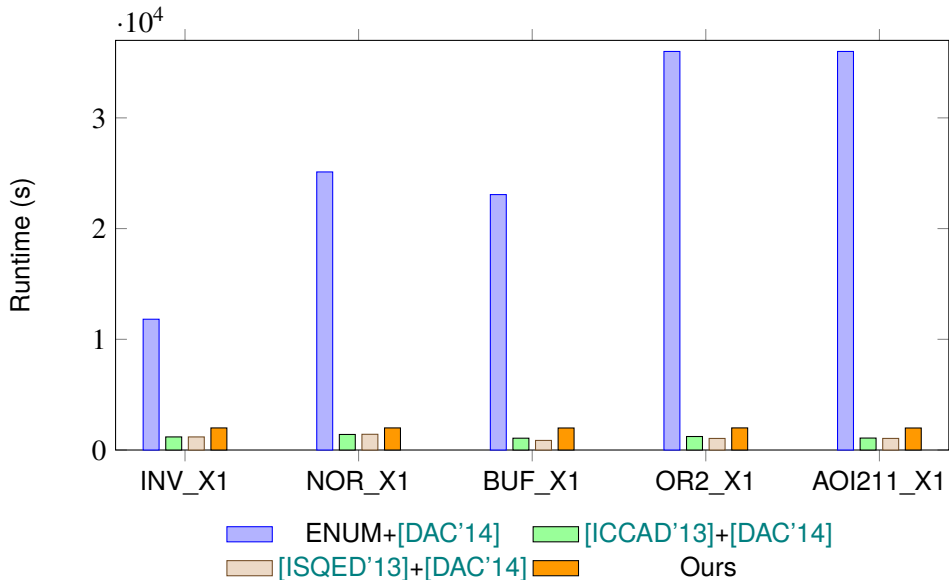
# #EPE Violation Convergence Curve



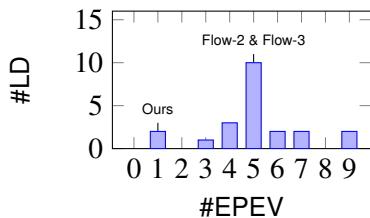
# Comparison – EPE Violation Num



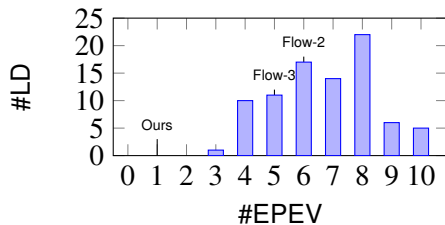
# Comparison – Runtime



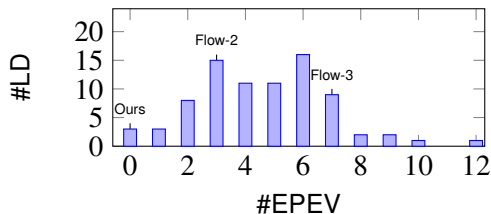
# Distribution of #EPEV violations



(a) BUF\_X1



(b) NAND4\_X1



(c) OR2\_X1

- ▶ Flow-2 [ICCAD'13] + [DAC'14];
- ▶ Flow-3 [ISQED'13] + [DAC'14];

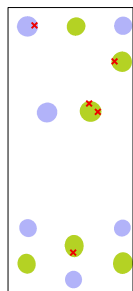


# Examples of Printed Image

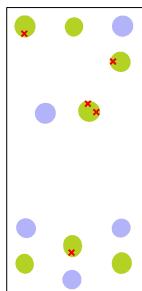
(a) [ICCAD'13] + [DAC'14];

(b) [ISQED'13] + [DAC'14];

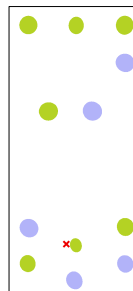
(c) Ours.



(a)



(b)



(c)

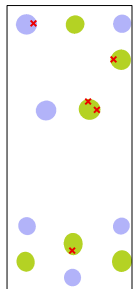
BUF\_X1

# Examples of Printed Image

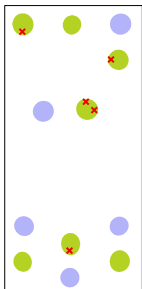
(a) [ICCAD'13] + [DAC'14];

(b) [ISQED'13] + [DAC'14];

(c) Ours.

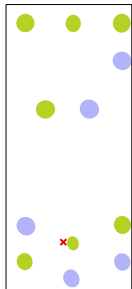


(a)

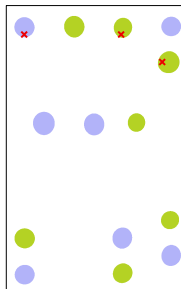


(b)

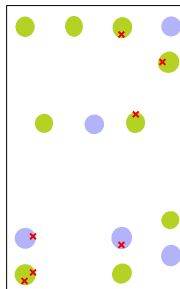
BUF\_X1



(c)

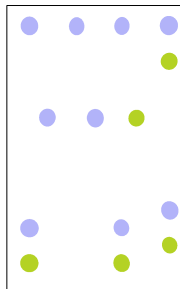


(a)



(b)

OR2\_X1



(c)

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# Conclusion

- ▶ A unified framework is proposed for solving LDMO problem.
- ▶ Two collaborative flows are designed:
  - ▶ A **gradient**-based numerical optimization
  - ▶ A set of **discrete** optimization.
- ▶ Effectiveness and efficiency are verified.

# Conclusion

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- ▶ Two collaborative flows are designed:
  - ▶ A **gradient**-based numerical optimization
  - ▶ A set of **discrete** optimization.
- ▶ Effectiveness and efficiency are verified.

## Future Exploration

- More advanced lithography process, e.g., **triple patterning lithography**.
- More optimization targets, such as **process variation band**.

# Thank You

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